



America Semiconductor

Silicon Bridge Rectifier

DB101G thru DB104G

$V_{RRM} = 50\text{ V} - 1000\text{ V}$

$I_F = 1\text{ A}$

Features

- Types up to 1000 V V_{RRM}
- Ideal for printed circuit board
- High surge current capability
- High temperature soldering guaranteed: 250°C/ 10 seconds
- Small size, simple installation

Mechanical Data

Case: Molded plastic

Polarity: Polarity symbols marked on body

Mounting position: Any

Terminals: Plated leads, solderable per MIL-STD-202

Method 208 guaranteed

DB Package



Maximum ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	DB101G	DB102G	DB103G	DB104G	Unit
Repetitive peak reverse voltage	V_{RRM}		50	100	200	400	V
RMS reverse voltage	V_{RMS}		35	70	140	280	V
DC blocking voltage	V_{DC}		50	100	200	400	V
Continuous forward current	I_F	$T_C \leq 40\text{ °C}$	1	1	1	1	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$, $t_p = 8.3\text{ ms}$	30	30	30	30	A
Operating temperature	T_j		-65 to 150	-65 to 150	-65 to 150	-65 to 150	°C
Storage temperature	T_{stg}		-65 to 150	-65 to 150	-65 to 150	-65 to 150	°C

Electrical characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	DB101G	DB102G	DB103G	DB104G	Unit
Diode forward voltage	V_F	$I_F = 1\text{ A}$, $T_j = 25\text{ °C}$	1.1	1.1	1.1	1.1	V
Reverse current	I_R	$V_R = 50\text{ V}$, $T_j = 25\text{ °C}$	5	5	5	5	μA
		$V_R = 50\text{ V}$, $T_j = 125\text{ °C}$	500	500	500	500	

Thermal characteristics

Parameter	Symbol	Conditions	DB101G	DB102G	DB103G	DB104G	Unit
Thermal resistance, junction - case	R_{thJC}		20.00	20.00	20.00	20.00	°C/W





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